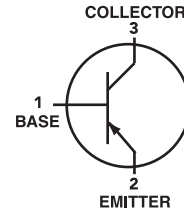


PNP General Purpose Transistors



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-25	Vdc
Collector-Base Voltage	V_{CBO}	-40	Vdc
Emitter-Base Voltage	V_{EBO}	-6.0	Vdc
Collector Current-Continuous	I_C	-1500	mAdc

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (1) $T_A=25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A=25^\circ\text{C}$ Derate above 25°C	P_D	625	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	5.0	$\text{mW}/^\circ\text{C}$
Junction and Storage, Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

DEVICE MARKING

SS8550=Y2

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
-----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C=-0.1\text{mAdc}, I_B=0$)	$V_{(BR)CEO}$	-25	-	Vdc
Collector-Base Breakdown Voltage ($I_C=-100\mu\text{Adc}, I_E=0$)	$V_{(BR)CBO}$	-40	-	Vdc
Emitter-Base Breakdown Voltage ($I_E=-100\mu\text{Adc}, I_C=0$)	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ($V_{CE}=-20\text{Vdc}, I_E=0$)	I_{CEO}	-	-0.1	μAdc
Collector Cutoff Current ($V_{CB}=-40\text{Vdc}, I_E=0$)	I_{CBO}	-	-0.1	μAdc
Emitter Cutoff Current ($V_{EB}=-5.0\text{Vdc}, I_C=0$)	I_{EBO}	-	-0.1	μAdc

1.FR-5=1.0 x 0.75 x 0.062 in

2.Alumina=0.4 x 0.3 x 0.024 in. 99.5% alumina

SS8550**QUNHAN TECH****ELECTRICAL CHARACTERISTICS** ($T_A=25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristics	Symbol	Min	Max	Unit
-----------------	--------	-----	-----	------

ON CHARACTERISTICS

DC Current Gain ($I_C=-100\text{ mAdc}$, $V_{CE}=1.0\text{ Vdc}$) ($I_C=-800\text{ mAdc}$, $V_{CE}=1.0\text{ Vdc}$)	$h_{FE}^{(1)}$ $h_{FE}^{(2)}$	120 40	350 -	- -
Collector-Emitter Saturation Voltage ($I_C=-800\text{ mAdc}$, $I_B=-80\text{ mAdc}$)	$V_{CE(sat)}$	-	-0.5	Vdc
Base-Emitter Saturation Voltage ($I_C=-800\text{ mAdc}$, $I_B=-80\text{ mAdc}$)	$V_{BE(sat)}$	-	-1.2	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product ($I_C=-50\text{ mAdc}$, $V_{CE}=-10\text{ Vdc}$, $f=30\text{ MHz}$)	f_T	100	-	MHz
---	-------	-----	---	-----

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	120-200	200-350

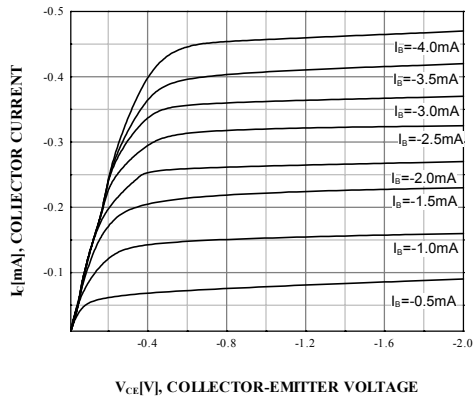


Figure 1. Static Characteristic

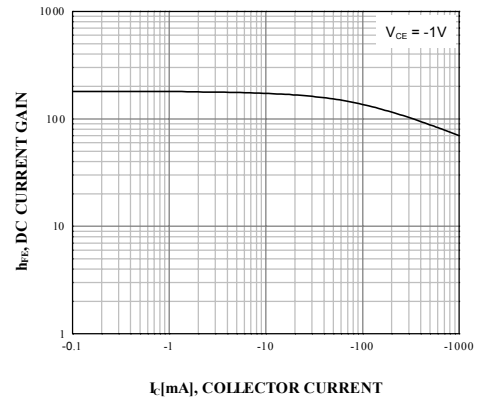


Figure 2. DC current Gain

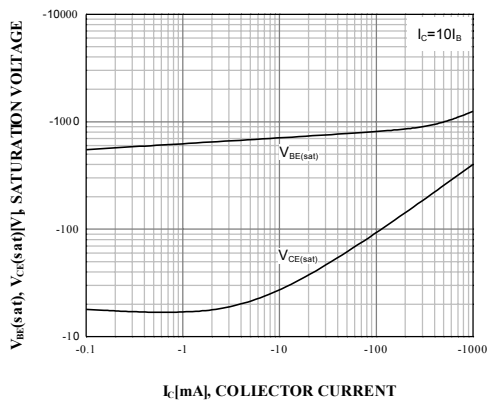


Figure 3. Base-Emitter Saturation Voltage
Collector-Emmitter Saturation Voltage

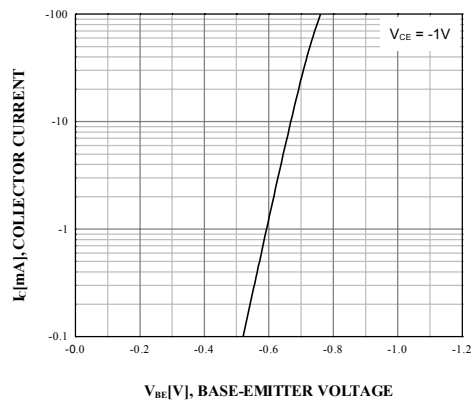


Figure 4. Base-Emitter On Voltage

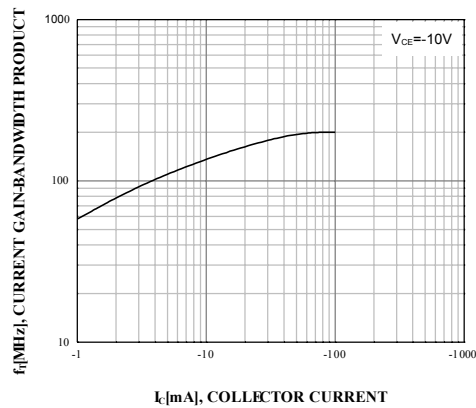


Figure 6. Current Gain Bandwidth Product

SS8550**QUNHAN TECH****ELECTRICAL CHARACTERISTICS** ($T_A=25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristics	Symbol	Min	Max	Unit
-----------------	--------	-----	-----	------

ON CHARACTERISTICS

DC Current Gain ($I_C=-100\text{ mAdc}$, $V_{CE}=1.0\text{ Vdc}$) ($I_C=-800\text{ mAdc}$, $V_{CE}=1.0\text{ Vdc}$)	$h_{FE}^{(1)}$ $h_{FE}^{(2)}$	120 40	350 -	- -
Collector-Emitter Saturation Voltage ($I_C=-800\text{ mAdc}$, $I_B=-80\text{ mAdc}$)	$V_{CE(sat)}$	-	-0.5	Vdc
Base-Emitter Saturation Voltage ($I_C=-800\text{ mAdc}$, $I_B=-80\text{ mAdc}$)	$V_{BE(sat)}$	-	-1.2	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product ($I_C=-50\text{ mAdc}$, $V_{CE}=-10\text{ Vdc}$, $f=30\text{ MHz}$)	f_T	100	-	MHz
---	-------	-----	---	-----

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	120-200	200-350

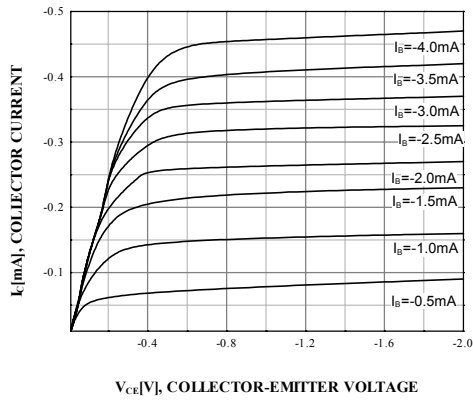


Figure 1. Static Characteristic

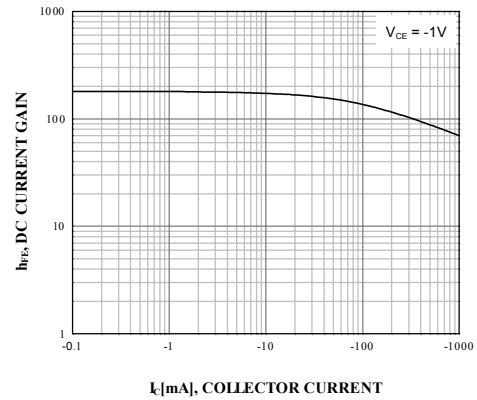


Figure 2. DC current Gain

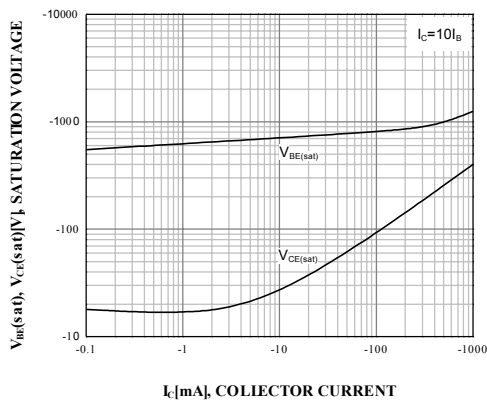


Figure 3. Base-Emitter Saturation Voltage
Collector-Emmitter Saturation Voltage

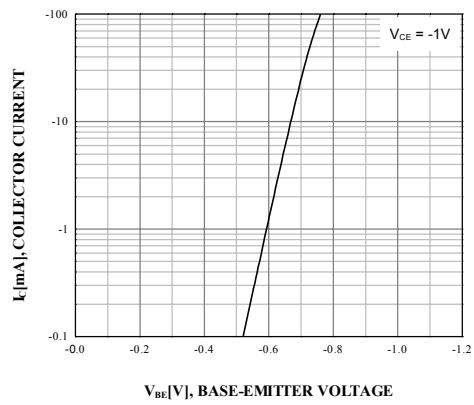


Figure 4. Base-Emitter On Voltage

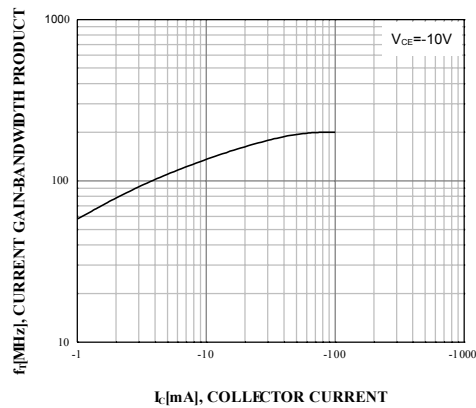


Figure 6. Current Gain Bandwidth Product